ISDN S Interface Transformer

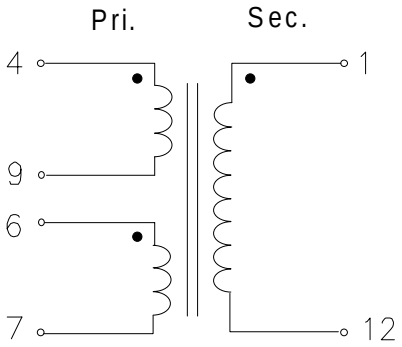
REINFORCED INSULATION PER EN 41003/EN 60950

Turns Ratio (± 5%)	1CT:2

PARAMETER	MIN.	MAX.	UNITS
Open Circuit Inductance	22		mHy
Leakage Inductance		15	µHy
Interwinding Capacitance ($C_{W/W}$)		60	pF
Primary DC Resistance		3.0	ohms
Secondary DC Resistance		5.5	ohms
Isolation (HI-POT)	3.0Kv		V_{RMS}

TEST CONDITIONS:
Oscillation Voltage = 700mV
Oscillation Frequency = 10.0 KHz
Inductance measured on Primary winding. Pins 4-7, short 9-6.

SCHEMATIC DIAGRAM

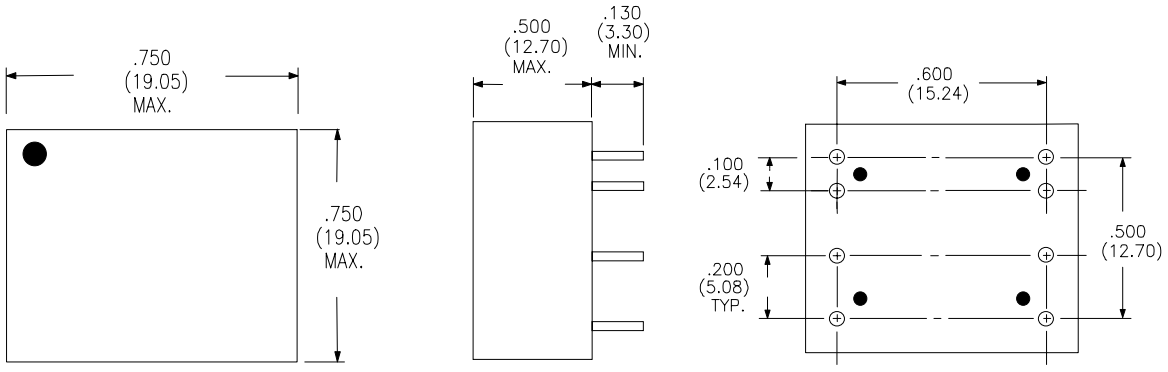


MEETS THE PULSE WAVEFORM TEMPLATE OF CCITT I.430.

Primary is Line Side

Unbalanced current at TE: Δ Idc = 5 mA max.
Longitudinal Conversion Loss - 10KHz to 300 KHz: 60dB min.

PHYSICAL DIMENSIONS
inches (mm)



Leads are #22 AWG Solderable

Unused Pins Omitted

Dot indicates pin #1

RHOMBUS P/N: **T-10459**	
CUST P/N:	NAME:
DATE: 07/02/96	SHEET: 1 OF 1

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